

## IN THE CLAIMS

Claims 8 - 18 have previously been canceled without prejudice as being drawn to a non-elected invention.

Please amend claims 1 and 19.

Please add new claims 24 - 26.

Please enter the pending claims as follows:

1. (Currently Amended) A ~~structure for devices~~ device comprising a multilayer stack of thin films, said thin films comprising a low-dielectric constant material, said thin films having pores, wherein each thin film within said multilayer stack has ~~the same a~~ thickness of less than about 20.0% of critical dimension (CD) of features in said device ~~devices~~.
2. (Original) The structure of claim 1 wherein said low-dielectric constant material comprises an inorganic oxide.
3. (Original) The structure of claim 2 wherein said inorganic oxide comprises Silicon Dioxide or silica.

4. (Original) The structure of claim 1 wherein said thin films have a porosity of below about 30.0 volume %.
5. (Original) The structure of claim 1 wherein said pores are embedded within said thin films.
6. (Original) The structure of claim 1 wherein said pores are unconnected.
7. (Original) The structure of claim 1 wherein said pores have a size on the order of 0.3-3.0 nanometers.
8. - 18. (Canceled)
19. (Currently Amended) A multilevel interconnect system for a device devices comprising:
  - an underlying metal level;
  - a multilayer stack disposed over said underlying metal level, said multilayer stack comprising:
    - thin films, said thin films having a low dielectric constant, said thin films having pores, wherein each thin film has ~~the same~~ a thickness of less than ~~about~~ 20.0% of critical dimension (CD) of features in said device ~~devices~~; and
    - an overlying metal level disposed over said multilayer stack.

20. (Previously Presented) The multilevel interconnect system of claim 19 wherein said thin films have a porosity of below about 30.0 volume %.
21. (Previously Presented) The multilevel interconnect system of claim 19 wherein said pores are embedded within said thin films.
22. (Original) The multilevel interconnect system of claim 19 wherein said pores are unconnected.
23. (Original) The multilevel interconnect system of claim 19 wherein said pores have a size on the order of 0.3 - 3.0 nanometers.
24. (New) A low-dielectric constant structure comprising a multilayer stack of thin films, said multilayer stack remaining stable up to 425.0 degrees Centigrade, said thin films comprising: an upper surface pore, an embedded pore, a lower surface pore, and a through pore, wherein said upper surface pores and said lower surface pores do not stack up over each other consecutively for more than 3 of said thin films.
25. (New) The low-dielectric constant structure of claim 24 wherein said thin films have a porosity of below 30.0 volume %.

26. (New) The low-dielectric constant structure of claim 24 wherein said pores have a size on the order of 0.3 - 3.0 nanometers.